

Amir Muhammad Afzal

List of Publications by Year in descending order

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19
papers

526
citations

759233

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557
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| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | High-Performance p-BP/n-PdSe ₂ Near-Infrared Photodiodes with a Fast and Gate-Tunable Photoresponse. ACS Applied Materials & Interfaces, 2020, 12, 19625-19634. | 8.0 | 67 |
| 2 | Highly Sensitive, Ultrafast, and Broadband Photo-Detecting Field-Effect Transistor with Transition-Metal Dichalcogenide van der Waals Heterostructures of MoTe ₂ and PdSe ₂ . Advanced Science, 2021, 8, e2003713. | 11.2 | 65 |
| 3 | Temperature-Dependent and Gate-Tunable Rectification in a Black Phosphorus/WS ₂ van der Waals Heterojunction Diode. ACS Applied Materials & Interfaces, 2018, 10, 13150-13157. | 8.0 | 61 |
| 4 | WS ₂ /GeSe/WS ₂ Bipolar Transistor-Based Chemical Sensor with Fast Response and Recovery Times. ACS Applied Materials & Interfaces, 2020, 12, 39524-39532. | 8.0 | 48 |
| 5 | Multifunctional and high-performance GeSe/PdSe ₂ heterostructure device with a fast photoresponse. Journal of Materials Chemistry C, 2020, 8, 4743-4753. | 5.5 | 47 |
| 6 | Tunneling-based rectification and photoresponsivity in black phosphorus/hexagonal boron nitride/rhenium diselenide van der Waals heterojunction diode. Nanoscale, 2020, 12, 3455-3468. | 5.6 | 40 |
| 7 | p-GeSe/n-ReS ₂ Heterojunction Rectifier Exhibiting A Fast Photoresponse with Ultra-High Frequency Switching Applications. Advanced Materials Interfaces, 2021, 8, 2100705. | 3.7 | 29 |
| 8 | Oxygen vacancies induced room temperature ferromagnetism and enhanced dielectric properties in Co and Mn co-doped ZnO nanoparticles. Journal of Materials Science: Materials in Electronics, 2021, 32, 9463-9474. | 2.2 | 28 |
| 9 | Formation of an MoTe ₂ based Schottky junction employing ultra-low and high resistive metal contacts. RSC Advances, 2019, 9, 10017-10023. | 3.6 | 27 |
| 10 | Ultrafast and Highly Stable Photodetectors Based on p-GeSe/n-ReSe ₂ Heterostructures. ACS Applied Materials & Interfaces, 2021, 13, 47882-47894. | 8.0 | 26 |
| 11 | Gate Tunable Transport in Graphene/MoS ₂ /(Cr/Au) Vertical Field-Effect Transistors. Nanomaterials, 2018, 8, 14. | 4.1 | 22 |
| 12 | Gate Modulation of the Spin-orbit Interaction in Bilayer Graphene Encapsulated by WS ₂ films. Scientific Reports, 2018, 8, 3412. | 3.3 | 20 |
| 13 | Fast and high photoresponsivity gallium telluride/hafnium selenide van der Waals heterostructure photodiode. Journal of Materials Chemistry C, 2021, 9, 7110-7118. | 5.5 | 10 |
| 14 | High performance and gate-controlled GeSe/HfS ₂ negative differential resistance device. RSC Advances, 2022, 12, 1278-1286. | 3.6 | 9 |
| 15 | Lamellar shape lead tungstate (PbWO ₄) nanostructures as synergistic catalyst for peroxidase mimetic activity. Materials Research Express, 2020, 7, 015520. | 1.6 | 7 |
| 16 | Ultraviolet-light-driven current modulation of Au/WS ₂ /Gr Schottky barrier. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 117, 113837. | 2.7 | 6 |
| 17 | A comparative study of electrical and opto-electrical properties of a few-layer p-WSe ₂ /n-WS ₂ heterojunction diode on SiO ₂ and h-BN substrates. RSC Advances, 2021, 11, 17901-17909. | 3.6 | 6 |
| 18 | Ultrasensitive V doped WO ₃ 1D nanorods heterojunction photodetector with pronounced photosensing activities. Journal of Alloys and Compounds, 2022, 909, 164753. | 5.5 | 5 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Enhancing the electronic properties of the graphene-based field-effect transistor via chemical doping of KBr. Journal of Materials Science: Materials in Electronics, 2022, 33, 12416-12425. | 2.2 | 3 |